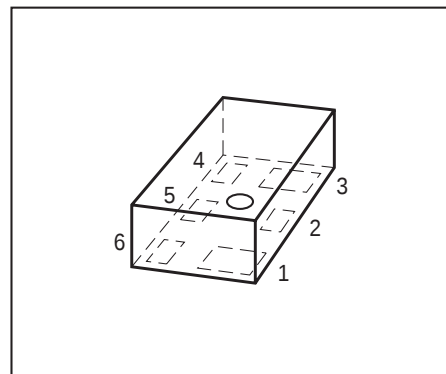
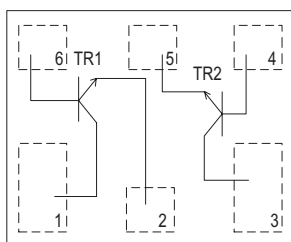


NPN Silicon RF TWIN Transistor*

- Low voltage/ low current applications
- Ideal for VCO modules and low noise amplifiers
- World's smallest SMD 6-pin leadless package
- Built in 2 transistors (TR1: die as BFR460L3,
TR2: die as BFR360L3)
- Low noise figure: TR1: 1.1dB at 1.8 GHz
TR2: 1.0 dB at 1.8 GHz
- TR1 with excellent ESD performance
typical value > 1500 V (HBM)
- Pb-free (RoHS compliant) package ¹⁾
- Qualified according AEC Q101

* Short term description



ESD (Electrostatic discharge) sensitive device, observe handling precaution!

Type	Marking	Pin Configuration						Package
BFS466L6	AC	1=C1	2=E1	3=C2	4=B2	5=E2	6=B1	TSLP-6-1

¹Pb-containing package may be available upon special request

Maximum Ratings

Parameter	Symbol	Value	Unit		
Collector-emitter voltage	V_{CEO}		V		
TR1, $T_A > 0\text{ }^{\circ}\text{C}$		4.5			
TR1, $T_A \leq 0\text{ }^{\circ}\text{C}$		4.2			
TR2, $T_A > 0\text{ }^{\circ}\text{C}$		6			
TR2, $T_A \leq 0\text{ }^{\circ}\text{C}$		6			
Collector-emitter voltage	V_{CES}				
TR1		15			
TR2		15			
Collector-base voltage	V_{CBO}				
TR1		15			
TR2		15			
Emitter-base voltage	V_{EBO}				
TR1		1.5			
TR2		2			
Collector current	I_C		mA		
TR1		50			
TR2		35			

Maximum Ratings

Parameter	Symbol	Value	Unit
Base current	I_B		mA
TR1		5	
TR2		4	
Total power dissipation ¹⁾	P_{tot}		mW
TR1, $T_S \leq 104^\circ\text{C}$		200	
TR2, $T_S \leq 102^\circ\text{C}$		210	
Junction temperature	T_j		$^\circ\text{C}$
TR1		150	
TR2		150	
Ambient temperature	T_A		
TR1		-65 ... 150	
TR2		-65 ... 150	
Storage temperature	T_{stg}		
TR1		-65 ... 150	
TR2		-65 ... 150	

Thermal Resistance

Parameter	Symbol	Value	Unit
Junction - soldering point ²⁾	R_{thJS}		K/W
TR1		≤ 230	
TR2		≤ 230	

¹⁾ T_S is measured on the collector lead at the soldering point to the pcb

²⁾ For calculation of R_{thJA} please refer to Application Note Thermal Resistance

Electrical Characteristics at $T_A = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
DC Characteristics					
Collector-emitter breakdown voltage TR1, $I_C = 1\text{ mA}$, $I_B = 0$ TR2, $I_C = 1\text{ mA}$, $I_B = 0$	$V_{(BR)CEO}$	4.5 6	5 9	- -	V
Collector-emitter cutoff current TR1, $V_{CE} = 15\text{ V}$, $V_{BE} = 0$ TR2, $V_{CE} = 15\text{ V}$, $V_{BE} = 0$	I_{CES}	- -	- -	10 10	μA
Collector-base cutoff current TR1, $V_{CB} = 5\text{ V}$, $I_E = 0$ TR2, $V_{CB} = 5\text{ V}$, $I_E = 0$	I_{CBO}	- -	- -	100 100	nA
Emitter-base cutoff current TR1, $V_{EB} = 0,5\text{ V}$, $I_C = 0$ TR2, $V_{EB} = 1\text{ V}$, $I_C = 0$	I_{EBO}	- -	- -	1 1	μA
DC current gain TR1, $I_C = 20\text{ mA}$, $V_{CE} = 3\text{ V}$, Pulse measured TR2, $I_C = 15\text{ mA}$, $V_{CE} = 3\text{ V}$, Pulse measured	h_{FE}	90 90	120 120	160 160	-

Electrical Characteristics at $T_A = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
AC Characteristics (verified by random sampling)					
Transition frequency	f_T				GHz
TR1, $I_C = 30\text{ mA}$, $V_{CE} = 3\text{ V}$, $f = 1\text{ GHz}$		16	22	-	
TR2, $I_C = 15\text{ mA}$, $V_{CE} = 3\text{ V}$, $f = 1\text{ GHz}$		11	14	-	
Collector-base capacitance	C_{cb}				pF
TR1, $V_{CB} = 3\text{ V}$, $f = 1\text{ MHz}$, $V_{BE} = 0$, emitter grounded		-	0.29	0.45	
TR2, $V_{CB} = 5\text{ V}$, $f = 1\text{ MHz}$, $V_{BE} = 0$, emitter grounded		-	0.26	0.4	
Collector emitter capacitance	C_{ce}				
TR1, $V_{CE} = 3\text{ V}$, $f = 1\text{ MHz}$, $V_{BE} = 0$, base grounded		-	0.14	-	
TR2, $V_{CE} = 5\text{ V}$, $f = 1\text{ MHz}$, $V_{BE} = 0$, base grounded		-	0.14	-	
Emitter-base capacitance	C_{eb}				
TR1, $V_{EB} = 0.5\text{ V}$, $f = 1\text{ MHz}$, $V_{CB} = 0$, collector grounded		-	0.54	-	
TR2, $V_{EB} = 0.5\text{ V}$, $f = 1\text{ MHz}$, $V_{CB} = 0$, collector grounded		-	0.43	-	

Electrical Characteristics at TA = 25°C, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
AC Characteristics (verified by random sampling)					
Noise figure	F				dB
TR1, $I_C=5\text{mA}$, $V_{CE} = 3\text{ V}$, $f = 1.8\text{ GHz}$, $Z_S = Z_{\text{Sopt}}$		-	1.1	-	
TR1, $I_C=5\text{mA}$, $V_{CE} = 3\text{ V}$, $f = 3\text{ GHz}$, $Z_S = Z_{\text{Sopt}}$		-	1.4	-	
TR2, $I_C=3\text{mA}$, $V_{CE} = 3\text{ V}$, $f = 1.8\text{ GHz}$, $Z_S = Z_{\text{Sopt}}$		-	1	-	
TR2, $I_C=3\text{mA}$, $V_{CE} = 3\text{ V}$, $f = 3\text{ GHz}$, $Z_S = Z_{\text{Sopt}}$		-	1.4	-	
Power gain, maximum available ¹⁾	G_{ma}				
TR1, $I_C = 20\text{ mA}$, $V_{CE} = 3\text{ V}$, $Z_S=Z_{\text{Sopt}}$, $Z_L=Z_{\text{Lopt}}$, $f = 1.8\text{ GHz}$		-	17	-	
TR1, $I_C = 20\text{ mA}$, $V_{CE} = 3\text{ V}$, $Z_S=Z_{\text{Sopt}}$, $Z_L=Z_{\text{Lopt}}$, $f = 3\text{ GHz}$		-	12	-	
TR2, $I_C = 15\text{ mA}$, $V_{CE} = 3\text{ V}$, $Z_S=Z_{\text{Sopt}}$, $Z_L=Z_{\text{Lopt}}$, $f = 1.8\text{ GHz}$		-	16.5	-	
TR2, $I_C = 15\text{ mA}$, $V_{CE} = 3\text{ V}$, $Z_S=Z_{\text{Sopt}}$, $Z_L=Z_{\text{Lopt}}$, $f = 3\text{ GHz}$		-	11.5	-	
Transducer gain	$ S_{21e} ^2$				
TR1, $I_C = 20\text{ mA}$, $V_{CE} = 3\text{ V}$, $Z_S = Z_L = 50\Omega$, $f = 1.8\text{GHz}$		-	14.5	-	
TR1, $I_C = 20\text{ mA}$, $V_{CE} = 3\text{ V}$, $Z_S = Z_L = 50\Omega$, $f = 3\text{GHz}$		-	10	-	
TR2, $I_C = 15\text{ mA}$, $V_{CE} = 3\text{ V}$, $Z_S = Z_L = 50\Omega$, $f = 1.8\text{GHz}$		-	13.5	-	
TR2, $I_C = 15\text{ mA}$, $V_{CE} = 3\text{ V}$, $Z_S = Z_L = 50\Omega$, $f = 3\text{GHz}$		-	9.5	-	
Third order intercept point at output ²⁾	IP_3				dBm
TR1, $V_{CE}=3\text{V}$, $I_C=20\text{mA}$, $Z_S=Z_L=50\Omega$, $f=1.8\text{GHz}$		-	28	-	
TR2, $V_{CE}=3\text{V}$, $I_C=15\text{mA}$, $Z_S=Z_L=50\Omega$, $f=1.8\text{GHz}$		-	24.5	-	
1dB Compression point, at output	$P_{-1\text{dB}}$				
TR1, $I_C=20\text{mA}$, $V_{CE}=3\text{V}$, $Z_S=Z_L=50\Omega$, $f=1.8\text{GHz}$		-	12	-	
TR1, $I_C=15\text{mA}$, $V_{CE}=3\text{V}$, $Z_S=Z_L=50\Omega$, $f=1.8\text{GHz}$		-	9	-	

¹⁾ $G_{\text{ma}} = |S_{21e}| / |S_{12e}| (k - (k^2 - 1)^{1/2})$
²⁾ IP_3 value depends on termination of all intermodulation frequency components.
Termination used for this measurement is 50Ω from 0.1 MHz to 6 GHz

Technical drawing of a mechanical part. The main view shows a rectangular part with a width of 8 and a height of 1.45. There are four circular features (holes) arranged in a row, with a center-to-center distance of 4. The distance from the left edge to the first hole is 1.05. A detail view on the right shows a cross-section of the part with a width of 0.5.

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